2N6449, 2N6450

N-Channel Silicon Junction Field-Effect Transistor

- **High Voltage**

Absolute maximum ratings at T_A = 25°C

	2N6449	2N6450
Reverse Gate Source Voltage	– 300 V	– 200 V
Reverse Gate Drain Voltage	– 300 V	– 200 V
Continuous Forward Gate Current	10 mA	10 mA
Continuous Device Power Dissipation	800 mW	800 mW
Power Derating	6.4 mW/°C	6.4 mW/°C

At 25°C free air temperature:		2N6449		2N6450		Process NJ42		
Static Electrical Characteristics		**Min**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 300		– 200		V	I_G = – 10 µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		– 100			nA	V_{GS} = – 150V, V_{DS} = ØV	
					– 100	nA	V_{GS} = – 100V, V_{DS} = ØV	
			– 100			µA	V_{GS} = – 150V, V_{DS} = ØV	T_A = 150°C
					– 100	µA	V_{GS} = – 100V, V_{DS} = ØV	T_A = 150°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 2	– 15	– 2	– 15	V	V_{DS} = 30V, I_D = 4 nA	
Drain Saturation Current (Pulsed)	I_{DSS}	2	10	2	10	mA	V_{DS} = 30V, V_{GS} = ØV	
Dynamic Electrical Characteristics								
Common Source Forward Transfer Admittance	Y_{fs}	0.5	3	0.5	3	mS	V_{DS} = 30V, V_{GS} = ØV	f = 1 kHz
Common Source Output Conductance	Y_{os}		100		100	µS	V_{DS} = 30V, V_{GS} = ØV	f = 1 kHz
Common Source Input Capacitance	C_{iss}		20		20	pF	V_{DS} = 30V, V_{GS} = ØV	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		2.5		2.5	pF	V_{DS} = 30V, V_{GS} = ØV	f = 1 MHz

TO-39 Package
Dimensions in Inches (mm)

Pin Configuration
1 Source, 2 Drain, 3 Gate & Case

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